

140 COMMERCE DRIVE MONTGOMERYVILLE, PA 18936-1013 PHONE: (215) 631-9840 FAX: (215) 631-9855

MS2475

RF & MICROWAVE TRANSISTORS AVIONICS APPLICATIONS

Features

- 1030 MHz
- COMMON BASE
- 30:1 LOAD VSWR CAPABILITY AT SPECIFIED LOAD
- CLASS C OPERATION
- POUT = 750W MIN.
- INTERNAL INPUT MATCH CONFIGURATION
- GOLD METALLIZATION

DESCRIPTION:

THE MS2475 IS A SILICON NPN BIPOLAR DEVICE SPECIFICALLY DESIGNED FOR HIGH PEAK PULSED POWER APPLICATIONS SUCH AS IFF AT 1030 MHz.

GOLD METALLIZATION AND EMITTER BALLASTING ASSURE HIGH RELIABILITY OPERATION UNDER CLASS C PULSED POWER AMPLIFIER OPERATION.







ASOLUTE MAXIMUM RATINGS (Tcase = 25°C)

Symbol	Parameter	Value	Unit
V _{сво}	Collector-Base Voltage	65	V
V _{CES}	Collector-Emitter Voltage	65	V
V _{EBO}	Emitter-Base Voltage	3.5	V
Ι _c	Device Current	40	Α
P _{DISS}	Power Dissipation	1350	W
TJ	Junction Temperature	+200	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Thermal Data

(TH(J-C)) outfolion base merinal resistance		R _{TH(J-C)}	Junction-case Thermal Resistance*	0.06	°C/W
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*Applies only to rated RF Amplifier Operation



MS2475

ELECTRICAL SPECIFICATIONS (Tcase = 25°C) STATIC

Symbol		Test Conditions		Value		
			Min.	Typ.	Max.	Unit
BV _{CBO}	I _c = 35mA	I _E = 0mA	65			V
BV _{CES}	I _E = 20mA	I _B =0mA	3.524			V
BV _{EBO}		I _C = 50mA	65			V
I _{CES}	V _{CB} = 52 V				35	mA
h _{FE}	$V_{CE} = 5 V$	$I_{\rm C} = 2A$	12.5		200	

DYNAMIC

Symbol	Test Conditions		Value				
				Min.	Typ.	Max.	Unit
Pout	f = 1030 MHz	V _{CE} = 52V	P _{IN} =150W	750			w
ης	f=1030MHz	V _{cc} =52	P _{IN} =150W	35			%
Droop	f =1030MHz	V _{cc} =52	P _{cc} =150W @25°C			1	dB

Pulse Width = 10 μ s Duty Cycle = 1 %



MS2475

PACKAGE MECHANICAL DATA



Advanced Power Technology reserves the right to change, without notice, the specifications and information contained herein Visit our website at **WWW.ADVANCEDPOWER.COM** or contact our factory direct.